

PROCESSING METHOD OF WAFER

ABSTRACT OF THE DISCLOSURE

A processing method of a wafer includes a trimming step of cutting the wafer along its outer peripheral edge while causing a cutting blade to cut from a front surface into a chamfered portion to a depth greater than a finish thickness, so that an annular stepped portion is formed in an outer peripheral surplus region, a protective member bonding step of bonding a protective member to a side of the front surface of the wafer, and a grinding step of grinding the wafer from its back surface to thin the wafer to the finish thickness. Between the trimming and grinding steps, a laser processing step is included to apply, to the stepped portion, a laser beam of a wavelength which has transmissivity for the wafer, so that annular modified layers are formed in the stepped portion.

[Fig. 7]